

Hitoshi Kubota

List of Publications by Year in descending order

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312
papers

12,874
citations

30070

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315
docs citations

315
times ranked

6161
citing authors

#	ARTICLE	IF	CITATIONS
1	Enhancing the interfacial perpendicular magnetic anisotropy and tunnel magnetoresistance by inserting an ultrathin LiF layer at an Fe/MgO interface. NPG Asia Materials, 2022, 14, .	7.9	10
2	Binding events through the mutual synchronization of spintronic nano-neurons. Nature Communications, 2022, 13, 883.	12.8	18
3	Perpendicular magnetic anisotropy and its voltage control in MgO/CoFeB/Mo/CoFeB/MgO junctions. Journal Physics D: Applied Physics, 2022, 55, 275003.	2.8	3
4	Perpendicular magnetic anisotropy and its electrical control in FeNiB ultrathin films. AIP Advances, 2021, 11, .	1.3	2
5	Reservoir Computing Leveraging the Transient Non-linear Dynamics of Spin-Torque Nano-Oscillators. Natural Computing Series, 2021, , 307-329.	2.2	4
6	Reservoir Computing Based on Spintronics Technology. Natural Computing Series, 2021, , 331-360.	2.2	7
7	Low frequency $1/f$ noise in deep submicrometer-sized magnetic tunnel junctions. Journal of Applied Physics, 2021, 129, .	2.5	2
8	Spin-torque dynamics for noise reduction in vortex-based sensors. Applied Physics Letters, 2021, 118, .	3.3	6
9	Recent progress in random number generator using voltage pulse-induced switching of nano-magnet: A perspective. APL Materials, 2021, 9, .	5.1	9
10	Low Gilbert damping in epitaxial thin films of the nodal-line semimetal $\text{D}_{05}\text{Fe}_3\text{Ga}$. Physical Review B, 2021, 103, .	3.2	5
11	Control of the stochastic response of magnetization dynamics in spin-torque oscillator through radio-frequency magnetic fields. Scientific Reports, 2021, 11, 16285.	3.3	5
12	Perpendicular magnetic anisotropy and its voltage control in MgO/CoFeB/MgO junctions with atomically thin Ta adhesion layers. Acta Materialia, 2021, 216, 117097.	7.9	19
13	Analysis method of a spin-torque oscillator using dc resistance change during injection locking to an external microwave magnetic field. Applied Physics Letters, 2021, 119, .	3.3	3
14	Giant charge-to-spin conversion in ferromagnet via spin-orbit coupling. Nature Communications, 2021, 12, 6254.	12.8	20
15	Large voltage-induced coercivity change in Pt/Co/CoO/amorphous TiOx structure and heavy metal insertion effect. Scientific Reports, 2021, 11, 21448.	3.3	5
16	Analysis of a Spin-Torque Oscillator Using Injection Locking to an External Microwave Field. , 2021, , .		0
17	Chaos in spin-torque oscillator with feedback circuit. Physical Review Research, 2021, 3, .	3.6	4
18	Randomly generated node-state-update procedure for dipole-coupled magnetic reservoir computing with voltage control of the magnetism. Journal Physics D: Applied Physics, 2020, 53, 094001.	2.8	1

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19	Voltage-Driven Magnetization Switching Controlled by Microwave Electric Field Pumping. Nano Letters, 2020, 20, 6012-6017.	9.1	14
20	Step-like dependence of memory function on pulse width in spintronics reservoir computing. Scientific Reports, 2020, 10, 19536.	3.3	18
21	Generation of charge current from magnetization oscillation via the inverse of voltage-controlled magnetic anisotropy effect. Science Advances, 2020, 6, eabc2618.	10.3	6
22	Influence of flicker noise and nonlinearity on the frequency spectrum of spin torque nano-oscillators. Scientific Reports, 2020, 10, 13116.	3.3	4
23	Spin-orbit torque generated from perpendicularly magnetized Co/Ni multilayers. Physical Review B, 2020, 101, .	3.2	16
24	Control of the magnetic domain of Pt/Co/Ru/MgO multilayer: Effect of Co thickness and Ru insertion. AIP Advances, 2020, 10, .	1.3	4
25	Voltage-Driven Magnetization Switching Using Inverse-Bias Schemes. Physical Review Applied, 2020, 13, .	3.8	18
26	Voltage-controlled magnetic anisotropy in an ultrathin Ir-doped Fe layer with a CoFe termination layer. APL Materials, 2020, 8, .	5.1	40
27	Role of non-linear data processing on speech recognition task in the framework of reservoir computing. Scientific Reports, 2020, 10, 328.	3.3	48
28	Temperature dependence of higher-order magnetic anisotropy constants and voltage-controlled magnetic anisotropy effect in a Cr/Fe/MgO junction. Japanese Journal of Applied Physics, 2020, 59, 010901.	1.5	6
29	Large Spin-Orbit-Torque Efficiency Generated by Spin Hall Effect in Paramagnetic Co - Ni - B Alloys. Physical Review Applied, 2020, 14, .	3.8	13
30	Periodic structure of memory function in spintronics reservoir with feedback current. Physical Review Research, 2020, 2, .	3.6	24
31	Evaluation of higher order magnetic anisotropy in a perpendicularly magnetized epitaxial ultrathin Fe layer and its applied voltage dependence. Japanese Journal of Applied Physics, 2019, 58, 090905.	1.5	10
32	CoFeB/MgO/CoFeB magnetic tunnel junctions prepared by layer-by-layer growth of naturally oxidized MgO. Applied Physics Express, 2019, 12, 103003.	2.4	1
33	Voltage-induced coercivity change in Co film grown on Cr ₂ O ₃ barrier. Japanese Journal of Applied Physics, 2019, 58, 100911.	1.5	3
34	Temporal Pattern Recognition with Delayed-Feedback Spin-Torque Nano-Oscillators. Physical Review Applied, 2019, 12, .	3.8	45
35	Low offset frequency flicker noise in spin-torque vortex oscillators. Physical Review B, 2019, 99, .		
36	Mutual Synchronization of Spin-Torque Nano-Oscillators Via Oersted Magnetic Fields Created by Waveguides. Physical Review Applied, 2019, 11, .	3.8	11

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37	Inducing out-of-plane precession of magnetization for microwave-assisted magnetic recording with an oscillating polarizer in a spin-torque oscillator. Applied Physics Letters, 2019, 114, .	3.3	16
38	Physical reservoir computing based on spin torque oscillator with forced synchronization. Applied Physics Letters, 2019, 114, .	3.3	106
39	Development of “spin dice” A Scalable Random Number Generator Based on Spin-Torque Switching. Spin, 2019, 09, 1940009.	1.3	2
40	Synchronization and chaos in a spin-torque oscillator with a perpendicularly magnetized free layer. Physical Review B, 2019, 100, .	3.2	14
41	Microwave amplification in a magnetic tunnel junction induced by heat-to-spin conversion at the nanoscale. Nature Nanotechnology, 2019, 14, 40-43.	31.5	26
42	Brownian motion of skyrmion bubbles and its control by voltage applications. Applied Physics Letters, 2019, 114, .	3.3	81
43	Write-Error Reduction of Voltage-Torque-Driven Magnetization Switching by a Controlled Voltage Pulse. Physical Review Applied, 2019, 11, .	3.8	32
44	Improvement of write error rate in voltage-driven magnetization switching. Journal Physics D: Applied Physics, 2019, 52, 164001.	2.8	36
45	10.1063/1.5070101.2. , 2019, , .		0
46	Development of Three-Dimensional Integration Technology for Magnetic Random Access Memories. Journal of Japan Institute of Electronics Packaging, 2019, 22, 495-500.	0.1	0
47	Integrated Reservoir Computing Module Using Magnetic Tunnel Junction. Journal of the Institute of Electrical Engineers of Japan, 2019, 139, 674-678.	0.0	0
48	Enhancement in the interfacial perpendicular magnetic anisotropy and the voltage-controlled magnetic anisotropy by heavy metal doping at the Fe/MgO interface. APL Materials, 2018, 6, .	5.1	53
49	Spin torque oscillator for microwave assisted magnetization reversal. Japanese Journal of Applied Physics, 2018, 57, 053001.	1.5	9
50	Neural-like computing with populations of superparamagnetic basis functions. Nature Communications, 2018, 9, 1533.	12.8	139
51	Giant magnetoresistance in perpendicularly magnetized synthetic antiferromagnetic coupling with Ir spacer. AIP Advances, 2018, 8, .	1.3	3
52	Spin-transfer torque induced by the spin anomalous Hall effect. Nature Electronics, 2018, 1, 120-123.	26.0	108
53	Effect of external magnetic field on locking range of spintronic feedback nano oscillator. AIP Advances, 2018, 8, .	1.3	3
54	Vector network analyzer ferromagnetic resonance spectrometer with field differential detection. Review of Scientific Instruments, 2018, 89, 053901.	1.3	16

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55	Reduction in the write error rate of voltage-induced dynamic magnetization switching using the reverse bias method. Japanese Journal of Applied Physics, 2018, 57, 040311.	1.5	18
56	Fabrication of Mg-X-O (X = Fe, Co, Ni, Cr, Mn, Ti, V, and Zn) barriers for magnetic tunnel junctions. AIP Advances, 2018, 8, .	1.3	8
57	Microwave Neural Processing and Broadcasting with Spintronic Nano-Oscillators. , 2018, , .		0
58	Low frequency noise in vortex spin torque nano-oscillators. , 2018, , .		0
59	Brain-Inspired Computing with Spintronics Devices. , 2018, , .		1
60	Magnetic Tunnel Junctions with a Nearly Zero Moment Manganese Nanolayer with Perpendicular Magnetic Anisotropy. ACS Applied Materials & Interfaces, 2018, 10, 43305-43310.	8.0	10
61	Macromagnetic Simulation for Reservoir Computing Utilizing Spin Dynamics in Magnetic Tunnel Junctions. Physical Review Applied, 2018, 10, .	3.8	97
62	Evaluation of memory capacity of spin torque oscillator for recurrent neural networks. Japanese Journal of Applied Physics, 2018, 57, 120307.	1.5	35
63	Vowel recognition with four coupled spin-torque nano-oscillators. Nature, 2018, 563, 230-234.	27.8	356
64	Scaling up electrically synchronized spin torque oscillator networks. Scientific Reports, 2018, 8, 13475.	3.3	49
65	Achievement of high diode sensitivity via spin torque-induced resonant expulsion in vortex magnetic tunnel junction. Applied Physics Express, 2018, 11, 053001.	2.4	23
66	Spin torque diode effect of the magnetic tunnel junction with MnGa free layer. Applied Physics Letters, 2018, 112, .	3.3	12
67	Self-Injection Locking of a Spin Torque Nano-Oscillator to Magnetic Field Feedback. Physical Review Applied, 2018, 10, .	3.8	11
68	Effect of Electric Field on the Exchange-Stiffness Constant in a $\text{Co}_{12}\text{Fe}_{16}$ Disk-Shaped Nanomagnet 65 nm in Diameter. Physical Review Applied, 2018, 10, .	3.8	11
69	Thermally Induced Precession-Orbit Transition of Magnetization in Voltage-Driven Magnetization Switching. Physical Review Applied, 2018, 10, .	3.8	29
70	Micromagnetic Simulations of Emission Power in Spin Torque Oscillator: Influence of Diameter and Interlayer Exchange Coupling. IEEE Transactions on Magnetics, 2018, 54, 1-5.	2.1	1
71	Mutual synchronization of spin-torque oscillators consisting of perpendicularly magnetized free layers and in-plane magnetized pinned layers. Applied Physics Express, 2018, 11, 013005.	2.4	17
72	Very strong antiferromagnetic interlayer exchange coupling with iridium spacer layer for perpendicular magnetic tunnel junctions. Applied Physics Letters, 2017, 110, .	3.3	65

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73	Three-dimensional integration technology of magnetic tunnel junctions for magnetoresistive random access memory application. Applied Physics Express, 2017, 10, 063002.	2.4	10
74	Mutual synchronization of spin torque nano-oscillators through a long-range and tunable electrical coupling scheme. Nature Communications, 2017, 8, 15825.	12.8	85
75	Accurate De-Embedding and Measurement of Spin-Torque Oscillators. IEEE Transactions on Magnetics, 2017, 53, 1-4.	2.1	3
76	Light-emitting-diode Lambertian light sources as low-radiant-flux standards applicable to quantitative luminescence-intensity imaging. Review of Scientific Instruments, 2017, 88, 093704.	1.3	7
77	Reduction in write error rate of voltage-driven dynamic magnetization switching by improving thermal stability factor. Applied Physics Letters, 2017, 111, .	3.3	60
78	Driven energy transfer between coupled modes in spin-torque oscillators. Physical Review B, 2017, 95, .	3.2	3
79	Neuromorphic computing with nanoscale spintronic oscillators. Nature, 2017, 547, 428-431.	27.8	893
80	Highly efficient voltage control of spin and enhanced interfacial perpendicular magnetic anisotropy in iridium-doped Fe/MgO magnetic tunnel junctions. NPG Asia Materials, 2017, 9, e451-e451.	7.9	84
81	Measurement of shot noise in magnetic tunnel junction and its utilization for accurate system calibration. Journal of Applied Physics, 2017, 122, .	2.5	4
82	Low-Energy Truly Random Number Generation with Superparamagnetic Tunnel Junctions for Unconventional Computing. Physical Review Applied, 2017, 8, .	3.8	106
83	Relaxation time and critical slowing down of a spin-torque oscillator. Physical Review B, 2017, 96, .	3.2	17
84	Physical Origin and Theoretical Limit of the Phase Stability of a Spin-Torque Oscillator Stabilized by a Phase-Locked Loop. Physical Review Applied, 2017, 7, .	3.8	2
85	Neuromorphic computing through time-multiplexing with a spin-torque nano-oscillator. , 2017, IEDM 2017, .		16
86	Integer, Fractional, and Sideband Injection Locking of a Spintronic Feedback Nano-Oscillator to a Microwave Signal. Physical Review Applied, 2017, 8, .	3.8	16
87	Voltage-Controlled Magnetic Anisotropy in an Ultrathin Fe Layer Sandwiched Between Cr and Mgo Layers. , 2016, , .		1
88	Evaluation of write error rate for voltage-driven dynamic magnetization switching in magnetic tunnel junctions with perpendicular magnetization. Applied Physics Express, 2016, 9, 013001.	2.4	87
89	Self-Injection Locking of a Vortex Spin Torque Oscillator by Delayed Feedback. Scientific Reports, 2016, 6, 26849.	3.3	40
90	Coherent microwave generation by spintronic feedback oscillator. Scientific Reports, 2016, 6, 30747.	3.3	31

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91	Microwave emission power exceeding $10^{1/4}$ W in spin torque vortex oscillator. Applied Physics Letters, 2016, 109, .	3.3	51
92	Spin-torque diode with tunable sensitivity and bandwidth by out-of-plane magnetic field. Applied Physics Letters, 2016, 108, 232407.	3.3	7
93	Diameter dependence of emission power in MgO-based nano-pillar spin-torque oscillators. Applied Physics Letters, 2016, 108, .	3.3	12
94	Extremely Coherent Microwave Emission from Spin Torque Oscillator Stabilized by Phase Locked Loop. Scientific Reports, 2016, 5, 18134.	3.3	51
95	Spin-wave eigenmodes in single disk-shaped FeB nanomagnet. Physical Review B, 2016, 94, .	3.2	9
96	A magnetic synapse: multilevel spin-torque memristor with perpendicular anisotropy. Scientific Reports, 2016, 6, 31510.	3.3	186
97	The effect of the MgO buffer layer thickness on magnetic anisotropy in MgO/Fe/Cr/MgO buffer/MgO(001). Journal of Applied Physics, 2016, 120, 085303.	2.5	8
98	Analysis of phase noise in a spin torque oscillator stabilized by phase locked loop. Applied Physics Express, 2016, 9, 053005.	2.4	10
99	Magnetic field angle dependence of out-of-plane precession in spin torque oscillators having an in-plane magnetized free layer and a perpendicularly magnetized reference layer. Applied Physics Express, 2016, 9, 053006.	2.4	13
100	Large Voltage-Induced Changes in the Perpendicular Magnetic Anisotropy of an MgO-Based Tunnel Junction with an Ultrathin Fe Layer. Physical Review Applied, 2016, 5, .	3.8	141
101	Instability analysis of spin-torque oscillator with an in-plane magnetized free layer and a perpendicularly magnetized pinned layer. Physical Review B, 2016, 93, .	3.2	25
102	Twist in the bias dependence of spin torques in magnetic tunnel junctions. Physical Review B, 2016, 93, .	3.2	5
103	Magnetization switching by current and microwaves. Physical Review B, 2016, 93, .	3.2	23
104	Influence of output power of a spin torque oscillator on phase locked loop operation. Japanese Journal of Applied Physics, 2016, 55, 093003.	1.5	3
105	Controlling the phase locking of stochastic magnetic bits for ultra-low power computation. Scientific Reports, 2016, 6, 30535.	3.3	32
106	Microwave detection based on magnetoresistance effect in spintronic devices. , 2016, , .		1
107	Multi-bits memory cell using degenerated magnetic states in a synthetic antiferromagnetic reference layer. Journal of Magnetism and Magnetic Materials, 2016, 400, 370-373.	2.3	0
108	Spin-torque resonant expulsion of the vortex core for an efficient radiofrequency detection scheme. Nature Nanotechnology, 2016, 11, 360-364.	31.5	75

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109	Perpendicular magnetic tunnel junction with enhanced anisotropy obtained by utilizing an Ir/Co interface. Applied Physics Express, 2016, 9, 013003.	2.4	22
110	Field angle dependence of voltage-induced ferromagnetic resonance under DC bias voltage. Journal of Magnetism and Magnetic Materials, 2016, 400, 159-162.	2.3	8
111	Understanding of Phase Noise Squeezing Under Fractional Synchronization of a Nonlinear Spin Transfer Vortex Oscillator. Physical Review Letters, 2015, 115, 017201.	7.8	50
112	Stable oscillation in spin torque oscillator excited by a small in-plane magnetic field. Journal of Applied Physics, 2015, 118, 053903.	2.5	9
113	Increased magnetic damping of a single domain wall and adjacent magnetic domains detected by spin torque diode in a nanostripe. Applied Physics Letters, 2015, 107, .	3.3	6
114	Underlayer material influence on electric-field controlled perpendicular magnetic anisotropy in CoFeB/MgO magnetic tunnel junctions. Physical Review B, 2015, 91, .	3.2	83
115	Generation of highly stable 5 GHz microwave from a spin torque oscillator by phase locked loop referenced to a 80 MHz clock. , 2015, , .		1
116	Spin dice (physical random number generator using spin torque switching) and its thermal response. , 2015, , .		4
117	Magnetic Stochastic Oscillators: Noise-Induced Synchronization to Underthreshold Excitation and Comprehensive Compact Model. IEEE Transactions on Magnetics, 2015, 51, 1-4.	2.1	18
118	Perpendicular magnetic anisotropy of Ir/CoFeB/MgO trilayer system tuned by electric fields. Applied Physics Express, 2015, 8, 053003.	2.4	73
119	Perpendicular magnetic tunnel junctions with strong antiferromagnetic interlayer exchange coupling at first oscillation peak. Applied Physics Express, 2015, 8, 083003.	2.4	53
120	Large amplitude oscillation of magnetization in spin-torque oscillator stabilized by field-like torque. Journal of Applied Physics, 2015, 117, 17C504.	2.5	6
121	Interface engineering using an Fe oxide insertion layer for growing a metastable bcc-Co on MgO(001). Applied Physics Letters, 2015, 106, 022405.	3.3	6
122	Three-Terminal Device for Realizing a Voltage-Driven Spin Transistor. IEEE Transactions on Magnetics, 2015, 51, 1-4.	2.1	0
123	Spin-torque diode spectrum of a spin valve with a synthetic antiferromagnetic reference layer. Japanese Journal of Applied Physics, 2014, 53, 123001.	1.5	6
124	Discontinuous frequency drop in spin torque oscillator with a perpendicularly magnetized FeB free layer. Japanese Journal of Applied Physics, 2014, 53, 060307.	1.5	6
125	Role of Magnetic Field in Self-Oscillation of Nanomagnet Excited by Spin Torque. IEEE Transactions on Magnetics, 2014, 50, 1-4.	2.1	2
126	Damping parameter and interfacial perpendicular magnetic anisotropy of FeB nanopillar sandwiched between MgO barrier and cap layers in magnetic tunnel junctions. Applied Physics Express, 2014, 7, 033004.	2.4	28

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127	High-output microwave detector using voltage-induced ferromagnetic resonance. Applied Physics Letters, 2014, 105, 192408.	3.3	23
128	Ultrahigh Sensitivity Ferromagnetic Resonance Measurement Based on Microwave Interferometer. IEEE Magnetics Letters, 2014, 5, 1-4.	1.1	19
129	Controlling the chirality and polarity of vortices in magnetic tunnel junctions. Applied Physics Letters, 2014, 105, .	3.3	28
130	Large amplitude spin torque vortex oscillations at zero external field using a perpendicular spin polarizer. Applied Physics Letters, 2014, 105, .	3.3	35
131	Noise-Enhanced Synchronization of Stochastic Magnetic Oscillators. Physical Review Applied, 2014, 2, .	3.8	48
132	Nonlinear Behavior and Mode Coupling in Spin-Transfer Nano-Oscillators. Physical Review Applied, 2014, 2, .	3.8	28
133	Observations of thermally excited ferromagnetic resonance on spin torque oscillators having a perpendicularly magnetized free layer. Journal of Applied Physics, 2014, 115, 17C740.	2.5	16
134	High Q factor over 3000 due to out-of-plane precession in nano-contact spin-torque oscillator based on magnetic tunnel junctions. Applied Physics Express, 2014, 7, 023003.	2.4	52
135	Highly sensitive nanoscale spin-torque diode. Nature Materials, 2014, 13, 50-56.	27.5	228
136	Theoretical Study of Spin-Torque Oscillator with Perpendicularly Magnetized Free Layer. IEEE Transactions on Magnetics, 2014, 50, 1-4.	2.1	14
137	Spin dice: A scalable truly random number generator based on spintronics. Applied Physics Express, 2014, 7, 083001.	2.4	174
138	Spintronic nano-oscillators: Towards nanoscale and tunable frequency devices. , 2014, , .		9
139	High emission power and Q factor in spin torque vortex oscillator consisting of FeB free layer. Applied Physics Express, 2014, 7, 063009.	2.4	58
140	Self-oscillation in spin torque oscillator stabilized by field-like torque. Applied Physics Letters, 2014, 104, .	3.3	27
141	Bias field angle dependence of the self-oscillation of spin torque oscillators having a perpendicularly magnetized free layer and in-plane magnetized reference layer. Applied Physics Express, 2014, 7, 063005.	2.4	19
142	Magnetization switching assisted by high-frequency-voltage-induced ferromagnetic resonance. Applied Physics Express, 2014, 7, 073002.	2.4	25
143	Response to noise of a vortex based spin transfer nano-oscillator. Physical Review B, 2014, 89, .	3.2	74
144	MgO overlayer thickness dependence of perpendicular magnetic anisotropy in CoFeB thin films. Journal of the Korean Physical Society, 2013, 62, 1461-1464.	0.7	21

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145	Future prospects of MRAM technologies. , 2013, , .		42
146	Parametric excitation of magnetic vortex gyrations in spin-torque nano-oscillators. Physical Review B, 2013, 88, .	3.2	23
147	Large Emission Power over 2 μ W with High Q Factor Obtained from Nanocontact Magnetic-Tunnel-Junction-Based Spin Torque Oscillator. Applied Physics Express, 2013, 6, 113005.	2.4	72
148	Enhanced Tunnel Magnetoresistance Effect in an Epitaxial Magnetic Tunnel Junction with a Hybrid $\text{Fe}_2\text{O}_3/\text{MgO}$ Barrier. Applied Physics Express, 2013, 6, 053005.	2.4	11
149	Radio-frequency amplification property of the MgO-based magnetic tunnel junction using field-induced ferromagnetic resonance. Applied Physics Letters, 2013, 102, 162409.	3.3	6
150	High domain wall velocities via spin transfer torque using vertical current injection. Scientific Reports, 2013, 3, 1829.	3.3	39
151	Voltage-Induced Magnetic Anisotropy Changes in an Ultrathin FeB Layer Sandwiched between Two MgO Layers. Applied Physics Express, 2013, 6, 073005.	2.4	52
152	Ultralow-Voltage Spin-Transfer Switching in Perpendicularly Magnetized Magnetic Tunnel Junctions with Synthetic Antiferromagnetic Reference Layer. Applied Physics Express, 2013, 6, 113006.	2.4	67
153	Effect of MgO Cap Layer on Gilbert Damping of FeB Electrode Layer in MgO-Based Magnetic Tunnel Junctions. Applied Physics Express, 2013, 6, 073002.	2.4	49
154	Critical Field of Spin Torque Oscillator with Perpendicularly Magnetized Free Layer. Applied Physics Express, 2013, 6, 123003.	2.4	48
155	Time-resolved observation of fast domain-walls driven by vertical spin currents in short tracks. Applied Physics Letters, 2013, 103, .	3.3	14
156	Spin-Torque Oscillator Based on Magnetic Tunnel Junction with a Perpendicularly Magnetized Free Layer and In-Plane Magnetized Polarizer. Applied Physics Express, 2013, 6, 103003.	2.4	144
157	Growth of a High-Quality Ultrathin Fe(001) Layer on MgO(001) by Insertion of an Ultrathin Fe_2O_3 Layer. Applied Physics Express, 2013, 6, 113004.	2.4	9
158	Nonlinear thermal effect on sub-gigahertz ferromagnetic resonance in magnetic tunnel junction. Applied Physics Letters, 2013, 103, .	3.3	3
159	Composition Dependence of Perpendicular Magnetic Anisotropy in $\text{Ta/Co}_x\text{Fe}_{80-x}\text{B}_{20}/\text{MgO}/\text{Ta}$ ($x=0, 10, 60$) Multilayers. Journal of Magnetism, 2013, 18, 5-8.	0.4	8
160	Spin-torque diode spectrum of ferromagnetically coupled (FeB/CoFe)/Ru/(CoFe/FeB) synthetic free layer. Journal of Applied Physics, 2012, 111, 07C917.	2.5	6
161	Quasi-omnidirectional electrical spectrometer for studying spin dynamics in magnetic tunnel junctions. Review of Scientific Instruments, 2012, 83, 024710.	1.3	4
162	Enhancement of perpendicular magnetic anisotropy in FeB free layers using a thin MgO cap layer. Journal of Applied Physics, 2012, 111, .	2.5	85

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163	Spin Torque Diode Spectroscopy of Quantized Spin Wave Excited in a Magnetic Tunnel Junction. IEEE Transactions on Magnetics, 2012, 48, 2816-2819.	2.1	6
164	Statistical Variance in Switching Probability of Spin-Torque Switching in MgO-MTJ. IEEE Transactions on Magnetics, 2012, 48, 4344-4346.	2.1	3
165	Pulse voltage-induced dynamic magnetization switching in magnetic tunneling junctions with high resistance-area product. Applied Physics Letters, 2012, 101, .	3.3	77
166	Electric-field-induced ferromagnetic resonance excitation in an ultrathin ferromagnetic metal layer. Nature Physics, 2012, 8, 491-496.	16.7	223
167	Temperature dependence of microwave voltage emission associated to spin-transfer induced vortex oscillation in magnetic tunnel junction. Applied Physics Letters, 2012, 100, .	3.3	23
168	Gain and Fan-Out in a Current-Field Driven Spin Transistor With an Assisting AC Magnetic Field. IEEE Transactions on Magnetics, 2012, 48, 1134-1138.	2.1	2
169	Spin-RAM for Normally-Off Computer. , 2011, , .		4
170	Spin control by application of electric current and voltage in FeCo/MgO junctions. Philosophical Transactions Series A, Mathematical, Physical, and Engineering Sciences, 2011, 369, 3658-3678.	3.4	14
171	Tunnel Magnetoresistance above 170% and Resistance Area Product of $1 \text{ } \hat{\text{C}} \text{ } (\hat{\text{A}}\mu\text{m})^2$ Attained by <i>In situ</i> Annealing of Ultra-Thin MgO Tunnel Barrier. Applied Physics Express, 2011, 4, 033002.	2.4	64
172	Spin-torque induced rf oscillation in magnetic tunnel junctions with an Fe-rich CoFeB free layer. Journal of Physics: Conference Series, 2011, 266, 012098.	0.4	9
173	Growth and magnetic properties of ultrathin $\text{Ni}_{1+x}\text{Fe}_2\text{O}_4$ films for spin filter junctions. Thin Solid Films, 2011, 519, 8239-8242.	1.8	4
174	High Spin-Torque Diode Sensitivity in CoFeB/MgO/CoFeB Magnetic Tunnel Junctions Under DC Bias Currents. IEEE Transactions on Magnetics, 2011, 47, 3373-3376.	2.1	17
175	Phase locking of vortex based spin transfer oscillators to a microwave current. Applied Physics Letters, 2011, 98, .	3.3	74
176	Switching-probability distribution of spin-torque switching in MgO-based magnetic tunnel junctions. Applied Physics Letters, 2011, 99, 112504.	3.3	11
177	Influence of Cu-Ni thickness on Peltier effect in submicron-sized Cu-Ni/Ru junctions. Journal of the Magnetics Society of Japan, 2011, 35, 264-267.	0.9	0
178	Large microwave generation from current-driven magnetic vortex oscillators in magnetic tunnel junctions. Nature Communications, 2010, 1, 8.	12.8	336
179	High efficient spin transfer torque writing on perpendicular magnetic tunnel junctions for high density MRAMs. Current Applied Physics, 2010, 10, e87-e89.	2.4	168
180	Enhancement of Thermal Stability Using Ferromagnetically Coupled Synthetic Free Layers in MgO-Based Magnetic Tunnel Junctions. IEEE Transactions on Magnetics, 2010, 46, 2232-2235.	2.1	15

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181	Spin-torque FMR and large rectification sensitivity in Fe-rich CoFeB-MgO magnetic tunnel junctions. , 2010, , .		0
182	Evaluation of barrier uniformity in magnetic tunnel junctions prepared using natural oxidation of thin Mg layers. Journal of Applied Physics, 2010, 108, 123915.	2.5	13
183	The effect of annealing on the junction profile of CoFeB/MgO tunnel junctions. Journal of Applied Physics, 2010, 108, 063922.	2.5	4
184	Giant Peltier Effect in a Submicron-Sized Cuâ€“Ni/Au Junction with Nanometer-Scale Phase Separation. Applied Physics Express, 2010, 3, 065204.	2.4	22
185	High Magnetoresistance Ratio and Low Resistanceâ€“Area Product in Magnetic Tunnel Junctions with Perpendicularly Magnetized Electrodes. Applied Physics Express, 2010, 3, 053003.	2.4	80
186	Spin-transfer-torque-induced rf oscillations in CoFeB/MgO/CoFeB magnetic tunnel junctions under a perpendicular magnetic field. Physical Review B, 2010, 81, .	3.2	36
187	Ultrathin Co/Pt and Co/Pd superlattice films for MgO-based perpendicular magnetic tunnel junctions. Applied Physics Letters, 2010, 97, .	3.3	255
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